

BUK762R6-60E

N-channel TrenchMOS standard level FET

28 July 2016

Product data sheet

1. General description

Standard level N-channel MOSFET in a SOT404 package using TrenchMOS technology. This product has been designed and qualified to AEC Q101 standard for use in high performance automotive applications.

2. Features and benefits

- AEC Q101 compliant
- Repetitive avalanche rated
- Suitable for thermally demanding environments due to 175 °C rating
- True standard level gate with V_{GS(th)} rating of greater than 1 V at 175 °C

3. Applications

- 12 V Automotive systems
- Electric and electro-hydraulic power steering
- Motors, lamps and solenoid control
- Start-Stop micro-hybrid applications
- Transmission control
- · Ultra high performance power switching

4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
V _{DS}	drain-source voltage	T _j ≥ 25 °C; T _j ≤ 175 °C		-	-	60	V
I _D	drain current	V _{GS} = 10 V; T _{mb} = 25 °C; <u>Fig. 2</u>	[1]	-	-	120	Α
P _{tot}	total power dissipation	T _{mb} = 25 °C; <u>Fig. 1</u>		-	-	324	W
Static charact	eristics						,
R _{DSon}	drain-source on-state resistance	$V_{GS} = 10 \text{ V}; I_D = 25 \text{ A}; T_j = 25 ^{\circ}\text{C};$ Fig. 11		_	1.97	2.6	mΩ
Dynamic characteristics							
Q_{GD}	gate-drain charge	I _D = 25 A; V _{DS} = 48 V; V _{GS} = 10 V; Fig. 13; Fig. 14		-	43.7	-	nC

[1] Continuous current is limited by package.



5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	G	gate	mb	D I
2	D	drain		
3	S	source		G—VIII
mb	D	mounting base; connected to drain	1 3	mbb076 S
			D2PAK (SOT404)	

6. Ordering information

Table 3. Ordering information

Type number	Package				
	Name	Description	Version		
BUK762R6-60E	D2PAK	plastic single-ended surface-mounted package (D2PAK); 3 leads (one lead cropped)	SOT404		

7. Marking

Table 4. Marking codes

Type number	Marking code
BUK762R6-60E	BUK762R6-60E

8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
V _{DS}	drain-source voltage	T _j ≥ 25 °C; T _j ≤ 175 °C		-	60	V
V_{DGR}	drain-gate voltage	R_{GS} = 20 k Ω		-	60	V
V_{GS}	gate-source voltage	T _j ≤ 175 °C; DC		-20	20	V
P _{tot}	total power dissipation	T _{mb} = 25 °C; <u>Fig. 1</u>		-	324	W
I _D	drain current	T _{mb} = 25 °C; V _{GS} = 10 V; <u>Fig. 2</u>	[1]	-	120	Α
		T _{mb} = 100 °C; V _{GS} = 10 V; <u>Fig. 2</u>	[1]	-	120	Α
I _{DM}	peak drain current	T_{mb} = 25 °C; pulsed; $t_p \le 10 \mu s$; Fig. 3		-	958	Α
T _{stg}	storage temperature			-55	175	°C
T _j	junction temperature			-55	175	°C

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Symbol	Parameter	Conditions		Min	Max	Unit
Source-dra	nin diode					
Is	source current	T _{mb} = 25 °C	[1]	-	120	Α
I _{SM}	peak source current	pulsed; $t_p \le 10 \ \mu s$; $T_{mb} = 25 \ ^{\circ}C$		-	958	Α
Avalanche	ruggedness					
E _{DS(AL)S}	non-repetitive drain-source avalanche energy	I_D = 120 A; $V_{sup} \le 60$ V; R_{GS} = 50 Ω; V_{GS} = 60 V; $T_{j(init)}$ = 25 °C; unclamped; Fig. 4	[2][3]	-	519	mJ

- Continuous current is limited by package. Single-pulse avalanche rating limited by maximum junction temperature of 175 $^{\circ}\text{C}.$
- Refer to application note AN10273 for further information.

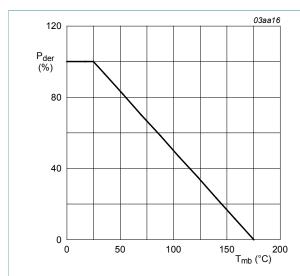
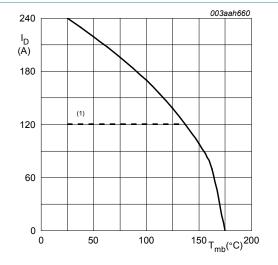


Fig. 1. Normalized total power dissipation as a function of mounting base temperature

$$P_{der} = \frac{P_{tot}}{P_{tot(25^{\circ}C)}} \times 100\%$$



(1) Capped at 120A due to package Fig. 2. Continuous drain current as a function of

mounting base temperature

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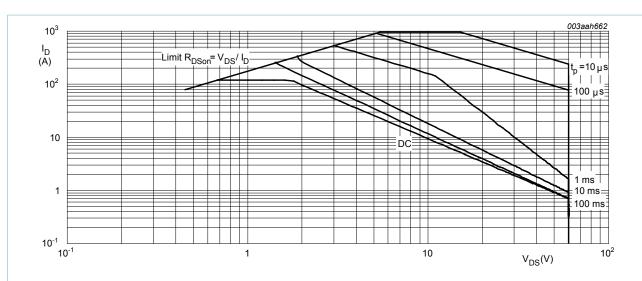
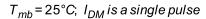


Fig. 3. Safe operating area; continuous and peak drain currents as a function of drain-source voltage



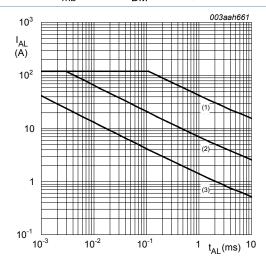


Fig. 4. Single pulse avalanche rating; avalanche current as a function of avalanche time

(1)
$$T_{j(init)} = 25$$
°C; (2) $T_{j(init)} = 150$ °C; (3) Repetitive Avalanche

9. Thermal characteristics

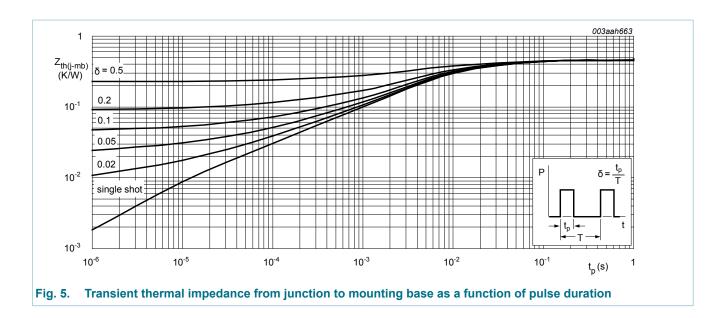
Table 6. Thermal characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
R _{th(j-mb)}	thermal resistance from junction to mounting base	Fig. 5	-	-	0.46	K/W
R _{th(j-a)}	thermal resistance from junction to ambient	minimum footprint ; mounted on a printed-circuit board	-	50	-	K/W

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10. Characteristics

Table 7. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static chara	acteristics			'		
V _{(BR)DSS}	drain-source	$I_D = 250 \mu A; V_{GS} = 0 V; T_j = 25 °C$	60	-	-	V
	breakdown voltage	$I_D = 250 \mu A; V_{GS} = 0 V; T_j = -55 °C$	54	-	-	V
V _{GS(th)}	gate-source threshold voltage	I _D = 1 mA; V _{DS} = V _{GS} ; T _j = 25 °C; Fig. 9; Fig. 10	2.4	3	4	V
		$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = 175 \text{ °C};$ Fig. 9	1	-	-	V
		$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = -55 \text{ °C};$ Fig. 9	-	-	4.5	V
I _{DSS} drain leakage curre	drain leakage current	V _{DS} = 60 V; V _{GS} = 0 V; T _j = 25 °C	-	0.09	1	μA
		V _{DS} = 60 V; V _{GS} = 0 V; T _j = 175 °C	-	-	500	μA
I _{GSS}	gate leakage current	V _{GS} = 20 V; V _{DS} = 0 V; T _j = 25 °C	-	2	100	nA
		V _{GS} = -20 V; V _{DS} = 0 V; T _j = 25 °C	-	2	100	nA
R _{DSon}	drain-source on-state resistance	V _{GS} = 10 V; I _D = 25 A; T _j = 25 °C; Fig. 11	-	1.97	2.6	mΩ
		V _{GS} = 10 V; I _D = 25 A; T _j = 175 °C; Fig. 11; Fig. 12	-	-	5.6	mΩ
Dynamic ch	naracteristics	1				
Q _{G(tot)}	total gate charge	I _D = 25 A; V _{DS} = 48 V; V _{GS} = 10 V;	-	140	-	nC
Q _{GS}	gate-source charge	Fig. 13; Fig. 14	-	32.7	-	nC
Q _{GD}	gate-drain charge		-	43.7	-	nC

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Symbol	Parameter	Conditions		Min	Тур	Max	Unit
C _{iss}	input capacitance	$V_{GS} = 0 \text{ V}; V_{DS} = 25 \text{ V}; f = 1 \text{ MHz};$ $T_j = 25 \text{ °C}; Fig. 15$		-	7629	10170	pF
C _{oss}	output capacitance			-	968	1160	pF
C _{rss}	reverse transfer capacitance			-	591	810	pF
t _{d(on)}	turn-on delay time	V_{DS} = 45 V; R_{L} = 1.8 Ω ; V_{GS} = 10 V; $R_{G(ext)}$ = 5 Ω		-	32	-	ns
t _r	rise time			-	50	-	ns
$t_{d(off)}$	turn-off delay time			-	87	-	ns
t _f	fall time			-	58	-	ns
L _D	internal drain inductance	from upper edge of mounting base to centre of die		-	2.5	-	nΗ
L _S	internal source inductance	measured from source lead to source bond pad		-	7.5	-	nH
Source-drai	in diode						,
V_{SD}	source-drain voltage	$I_S = 25 \text{ A}; V_{GS} = 0 \text{ V}; T_j = 25 ^{\circ}\text{C}; Fig. 16$		-	0.78	1.2	V
t _{rr}	reverse recovery time	$I_S = 20 \text{ A}; dI_S/dt = -100 \text{ A/}\mu\text{s}; V_{GS} = 0 \text{ V};$		-	44	-	ns
Q _r	recovered charge	V _{DS} = 25 V		-	67	-	nC

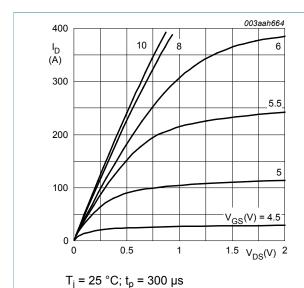


Fig. 6. Output characteristics; drain current as a function of drain-source voltage; typical values

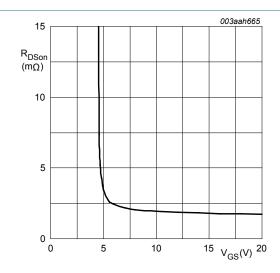


Fig. 7. Drain-source on-state resistance as a function of gate-source voltage; typical values

$$T_j = 25$$
°C; $I_D = 25A$

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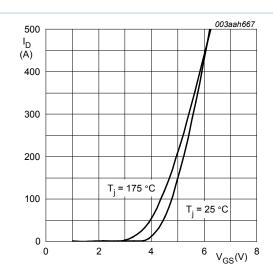


Fig. 8. Transfer characteristics; drain current as a function of gate-source voltage; typical values



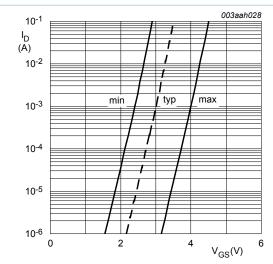


Fig. 10. Sub-threshold drain current as a function of gate-source voltage

$$T_j = 25^{\circ}C; \ V_{DS} = 5V$$

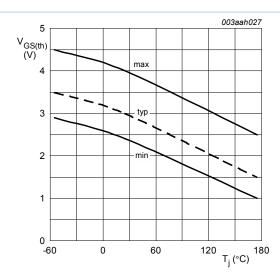


Fig. 9. Gate-source threshold voltage as a function of junction temperature

$$I_D$$
 = 1 mA; V_{DS} = V_{GS}

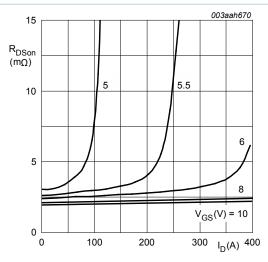


Fig. 11. Drain-source on-state resistance as a function of drain current; typical values

 $T_i = 25 \, ^{\circ}C; t_p = 300 \, \mu s$

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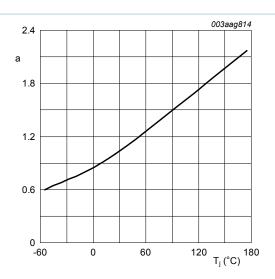


Fig. 12. Normalized drain-source on-state resistance factor as a function of junction temperature

$$a = \frac{R_{DSon}}{R_{DSon(25 \, ^{\circ}\text{C})}}$$

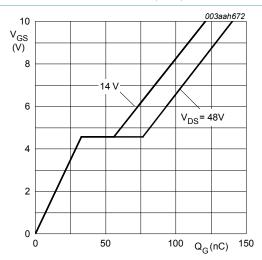


Fig. 14. Gate-source voltage as a function of gate charge; typical values

$$T_j = 25^{\circ}C; I_D = 25A$$

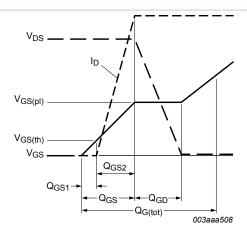


Fig. 13. Gate charge waveform definitions

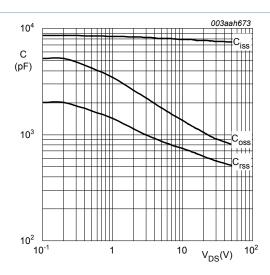


Fig. 15. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values

$$V_{GS} = 0V$$
; $f = 1MHz$

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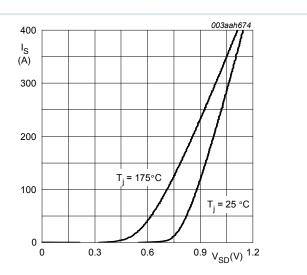
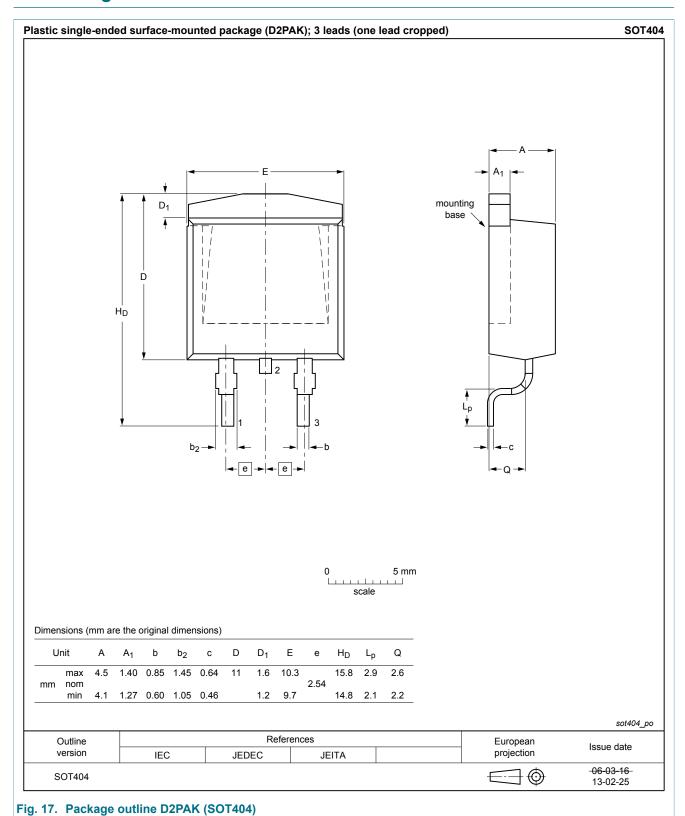


Fig. 16. Source (diode forward) current as a function of source-drain (diode forward) voltage; typical values $V_{\rm GS} = 0V$

11. Package outline



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